



## SOT-23 Plastic-Encapsulate Transistors

**A733LT1**

TRANSISTOR ( PNP )

### FEATURES

Power dissipation

$$P_{CM} : 0.2 \text{ W ( } T_{amb}=25 \text{ )}$$

Collector current

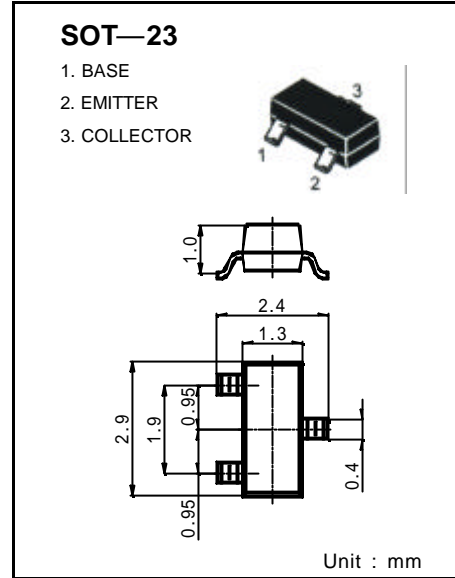
$$I_{CM} : -0.15 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -60 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55 \text{ to } +150$$



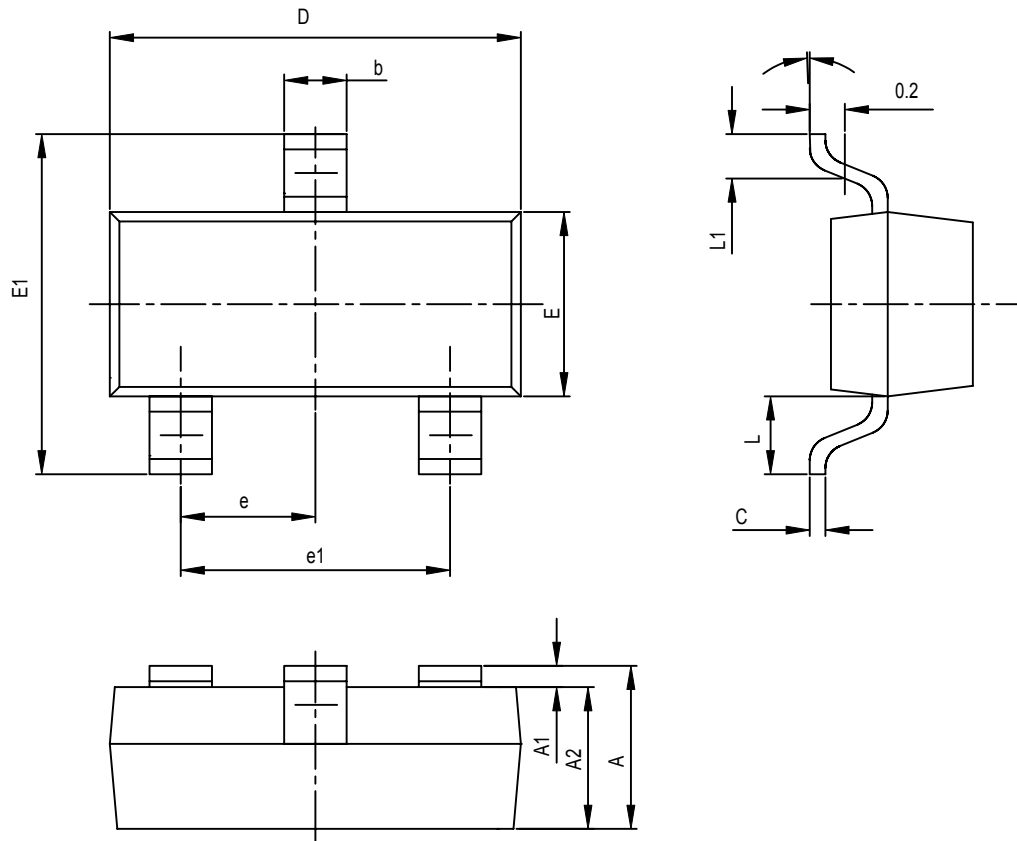
### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25$ unless otherwise specified )

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -5 \mu A, I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 \text{ mA}, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50 \mu A, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -60 \text{ V}, I_E = 0$			-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5 \text{ V}, I_C = 0$			-0.1	$\mu A$
DC current gain	$H_{FE(1)}$	$V_{CE} = -6 \text{ V}, I_C = -1 \text{ mA}$	120		475	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$		-0.18	-0.3	V
Transition frequency	$f_T$	$V_{CE} = -6 \text{ V}, I_C = -10 \text{ mA}$ $f = 30 \text{ MHz}$	50			MHz

### CLASSIFICATION OF $H_{FE(1)}$

Rank	L	H
Range	120-200	200-475
MARKING	CS	

## SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
<b>A</b>	0.900	1.100	0.035	0.043
<b>A1</b>	0.000	0.100	0.000	0.004
<b>A2</b>	0.900	1.000	0.035	0.039
<b>b</b>	0.300	0.500	0.012	0.020
<b>c</b>	0.080	0.150	0.003	0.006
<b>D</b>	2.800	3.000	0.110	0.118
<b>E</b>	1.200	1.400	0.047	0.055
<b>E1</b>	2.250	2.550	0.089	0.100
<b>e</b>	0.950TPY		0.037TPY	
<b>e1</b>	1.800	2.000	0.071	0.079
<b>L</b>	0.550REF		0.022REF	
<b>L1</b>	0.300	0.500	0.012	0.020
$\theta$	0°	8°	0°	8°